

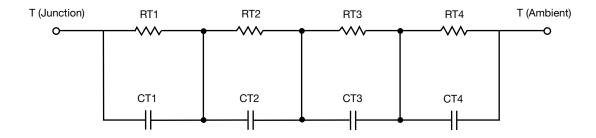
# **R-C Thermal Model Parameters**

### **DESCRIPTION**

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. R-C values for the electrical circuit in the Foster/tank and Cauer/filter configurations are included. When implemented in P-SPICE, these values have matching characteristic curves to the single-pulse transient thermal impedance curves for the MOSFET.

These RC values can be used in the P-SPICE simulation to evaluate the thermal behavior of the MOSFET junction temperature under a defined power profile. These techniques are described in application note AN609, "Thermal Simulation of Power MOSFETs on the P-SPICE Platform".

### **R-C THERMAL MODEL FOR TANK CONFIGURATION**



R-C VALUES FOR TANK CONFIGURATION  THERMAL RESISTANCE (°C/W)					
RT1	N/A	95.9591m	N/A		
RT2	N/A	69.9012m	N/A		
RT3	N/A	43.3938m	N/A		
RT4	N/A	190.7459m	N/A		
	THERMAL CAPAC	CITANCE (Joules/°C)			
Junction to	Ambient	Case	Foot		
CT1	N/A	131.4025m	N/A		
CT2	N/A	19.0813m	N/A		
CT3	N/A	656.8161u	N/A		
CT4	N/A	301.8310m	N/A		

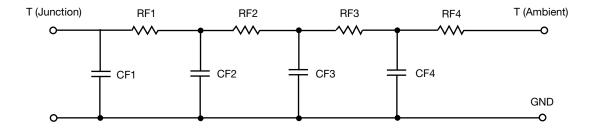
#### Note

• n/a indicates not applicable

This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



# **R-C THERMAL MODEL FOR FILTER CONFIGURATION**



R-C VALUES FOR FILTER CONFIGURATION						
THERMAL RESISTANCE (°C/W)						
Junction to	Ambient	Case	Foot			
RF1	N/A	56.9202m	N/A			
RF2	N/A	119.8712m	N/A			
RF3	N/A	66.3875m	N/A			
RF4	N/A	155.7679m	N/A			
	THERMAL CAPAC	CITANCE (Joules/°C)				
Junction to	Ambient	Case	Foot			
CF1	N/A	1.0616m	N/A			
CF2	N/A	23.2369m	N/A			
CF3	N/A	166.4858m	N/A			
CF4	N/A	647.4969u	N/A			

## Note

• n/a indicates not applicable





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